

N-Channel Super Junction Power MOSFET II

General Description

The series of devices use advanced super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

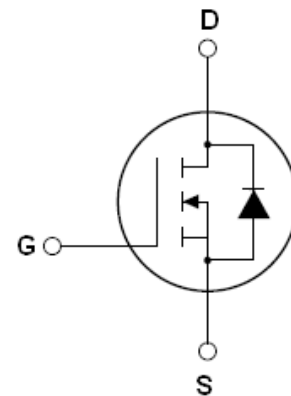
Features

- New technology for high voltage device
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

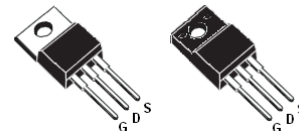
V_{DS}	800	V
$R_{DS(ON)}$ TYP.	280	m Ω
I_D	18	A



Schematic diagram

Package Marking And Ordering Information

Device	Device Package	Marking
HMS18N80	TO-220	HMS18N80
HMS18N80F	TO-220F	HMS18N80F



TO-220 T O-220F

Table 1. Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Parameter	Symbol	HMS18N80	HMS18N80F	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	800		V
Gate-Source Voltage ($V_{DS}=0V$)	V_{GS}	± 30		V
Continuous Drain Current at $T_c=25^\circ\text{C}$	$I_{D(DC)}$	18	18*	A
Continuous Drain Current at $T_c=100^\circ\text{C}$	$I_{D(DC)}$	115	115	A
Pulsed drain current (Note 1)	$I_{DM(pluse)}$	54	54	A
Maximum Power Dissipation($T_c=25^\circ\text{C}$)	P_D	200	34	W
Derate above 25°C		1.6	0.27	W/ $^\circ\text{C}$
Single pulse avalanche energy (Note 2)	E_{AS}	690		mJ
Avalanche current (Note 1)	I_{AR}	7		A
Repetitive Avalanche energy, t_{AR} limited by T_{jmax} (Note 1)	E_{AR}	1		mJ

Parameter	Symbol	NCE70R180	NCE70R180F	Unit
Drain Source voltage slope, $V_{DS} \leq 480V$,	dv/dt	50		V/ns
Reverse diode dv/dt, $V_{DS} \leq 480V, I_{SD} < I_D$	dv/dt	15		V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55...+150		°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	NCE70R180	NCE70R180F	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	0.62	3.67	°C /W
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	62.5	80	°C /W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	800			V
Zero Gate Voltage Drain Current($T_C=25^\circ C$)	I_{DSS}	$V_{DS}=800V, V_{GS}=0V$		0.05	1	μA
Zero Gate Voltage Drain Current($T_C=125^\circ C$)	I_{DSS}	$V_{DS}=800V, V_{GS}=0V$			100	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 30V, V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5		4.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=10.5A$			280	m Ω
Dynamic Characteristics						
Forward Transconductance	g_{FS}	$V_{DS} = 20V, I_D = 10.5A$		17.5		S
Input Capacitance	C_{ISS}	$V_{DS}=50V, V_{GS}=0V,$ $F=1.0MHz$		1950		PF
Output Capacitance	C_{OSS}			150		PF
Reverse Transfer Capacitance	C_{RSS}			5		PF
Total Gate Charge	Q_g	$V_{DS}=480V, I_D=18A,$ $V_{GS}=10V$		45	70	nC
Gate-Source Charge	Q_{gs}			9		nC
Gate-Drain Charge	Q_{gd}			18		nC
Intrinsic gate resistance	R_G	$f = 1 MHz$ open drain		1		Ω
Switching times						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=380V, I_D=11A,$ $R_G=4\Omega, V_{GS}=10V$		11		nS
Turn-on Rise Time	t_r			6		nS
Turn-Off Delay Time	$t_{d(off)}$			61	100	nS
Turn-Off Fall Time	t_f			4.5	12	nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	$T_C=25^\circ C$			18	A
Pulsed Source-drain current(Body Diode)	I_{SDM}				54	A
Forward on voltage	V_{SD}	$T_J=25^\circ C, I_{SD}=18A, V_{GS}=0V$		0.9	1.3	V
Reverse Recovery Time	t_{rr}	$T_J=25^\circ C, I_F=18A, di/dt=100A/\mu s$		310		nS
Reverse Recovery Charge	Q_{rr}				5	μC
Peak Reverse Recovery Current	I_{rrm}				28	A

Notes 1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_J=25^\circ C, V_{DD}=50V, V_G=10V, R_G=25\Omega$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area for TO-220

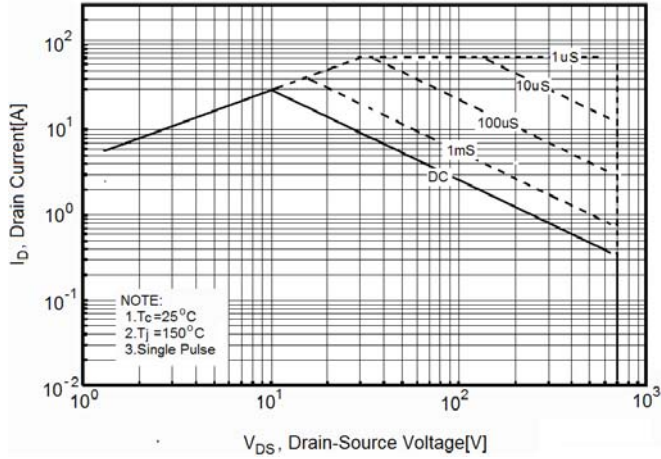


Figure2. Safe operating area for TO-220F

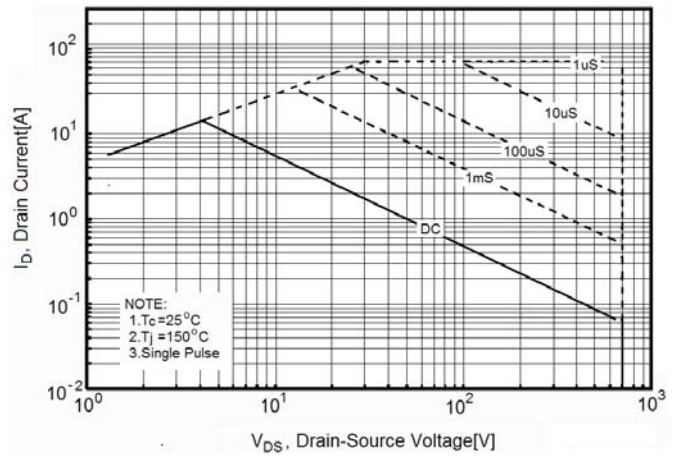


Figure3. Source-Drain Diode Forward Voltage

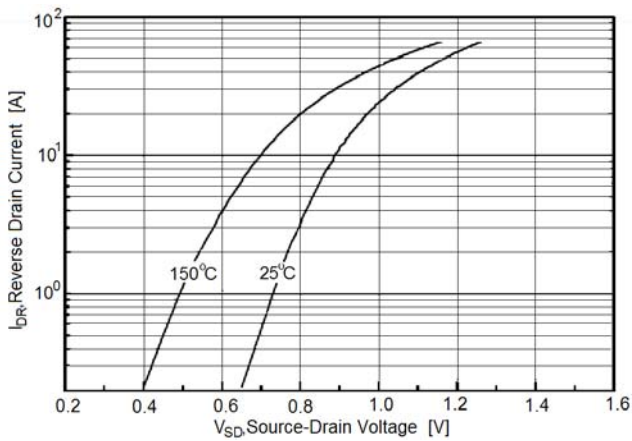


Figure4. Output characteristics

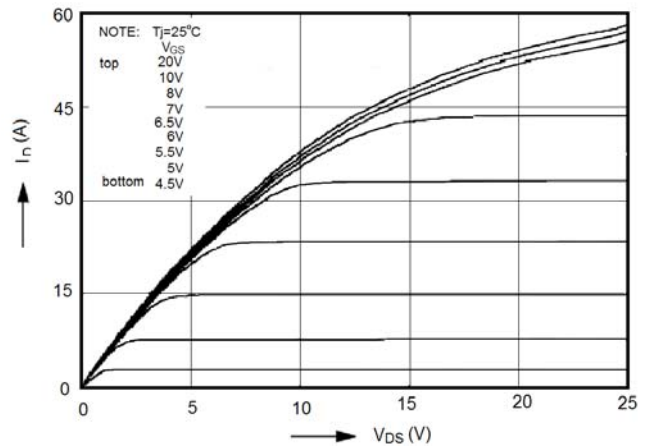


Figure5. Transfer characteristics

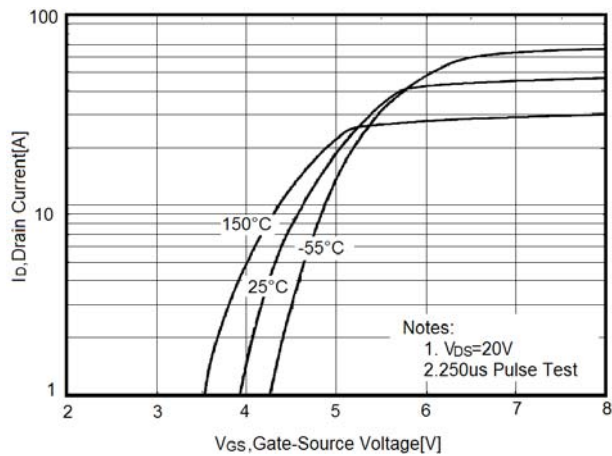


Figure6. Static drain-source on resistance

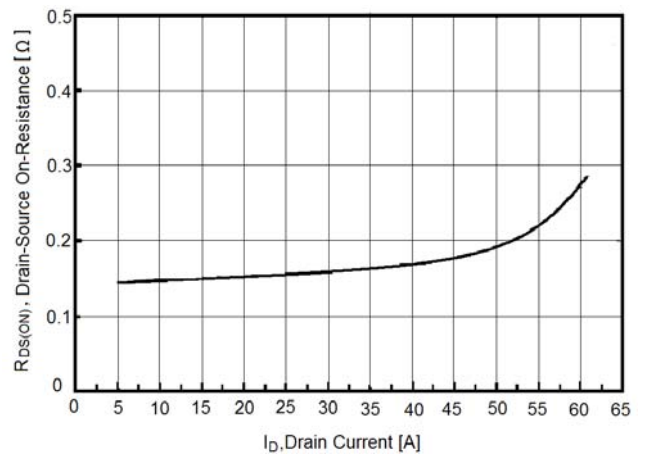


Figure7. $R_{DS(ON)}$ vs Junction Temperature

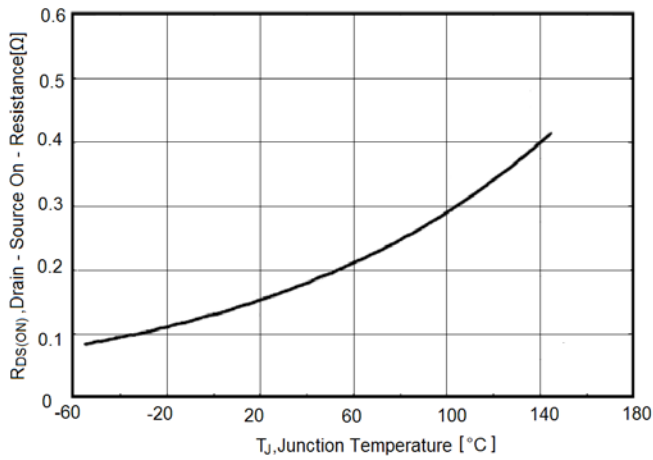


Figure8. BV_{DSS} vs Junction Temperature

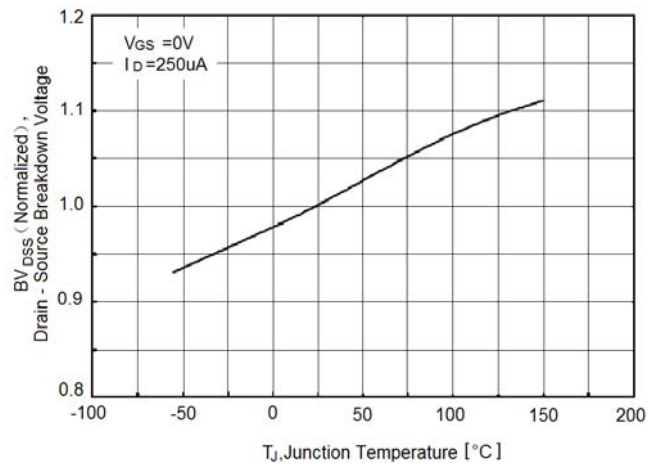


Figure9. Maximum I_D vs Junction Temperature

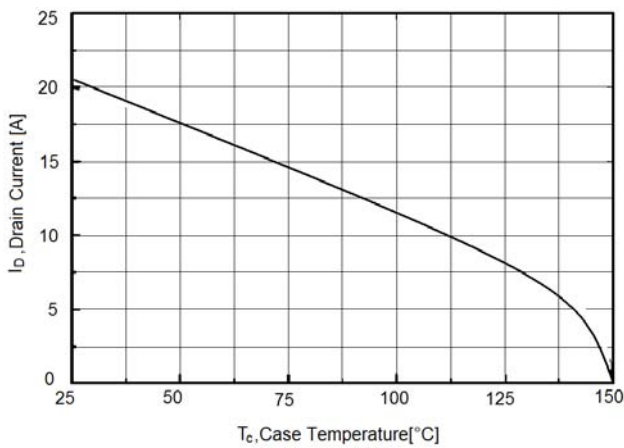


Figure10. Gate charge waveforms

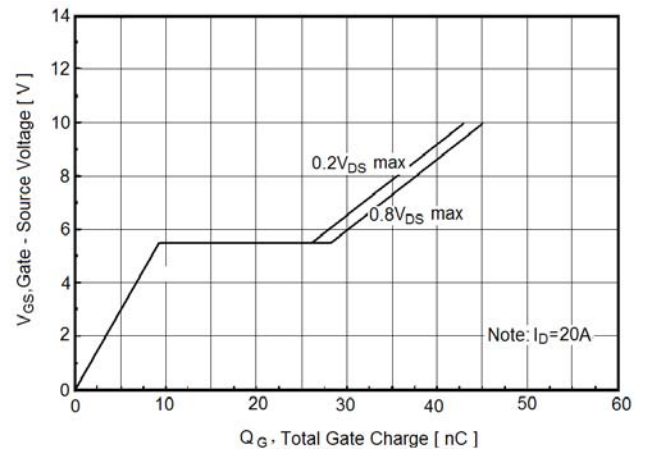


Figure11. Capacitance

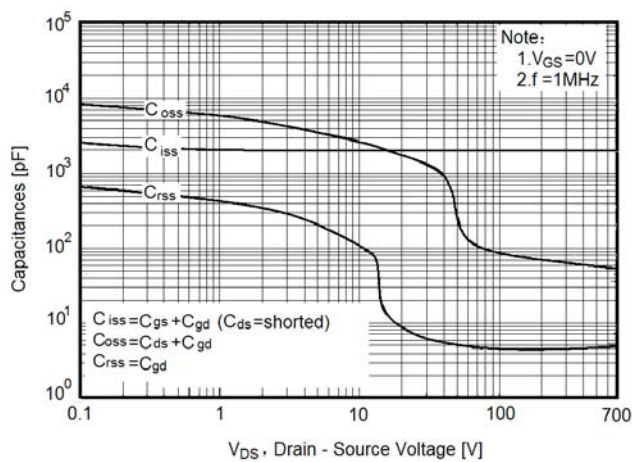


Figure12. Transient Thermal Impedance for TO-220

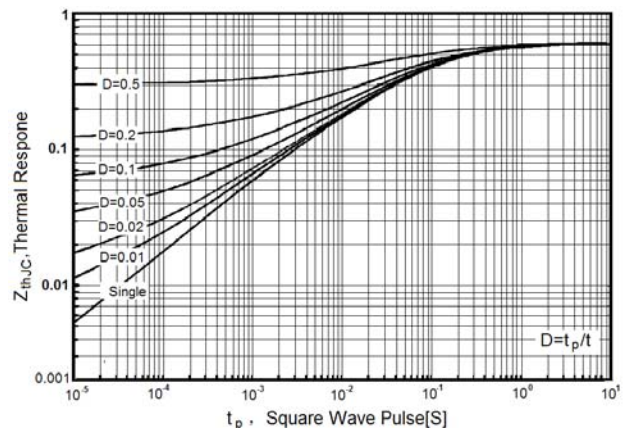
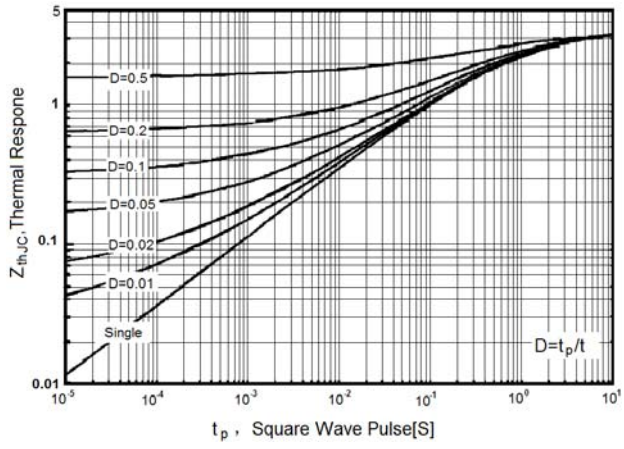
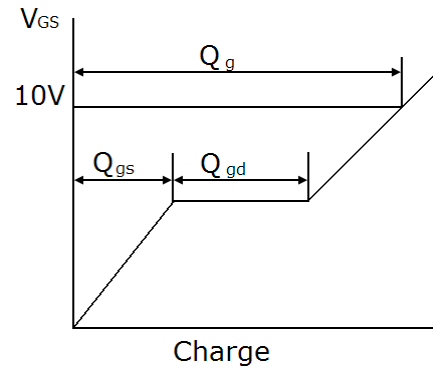
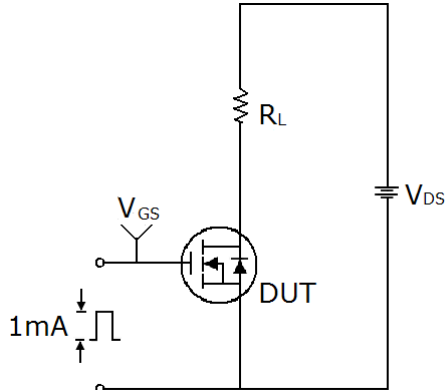


Figure13. Transient Thermal Impedance for TO-220F

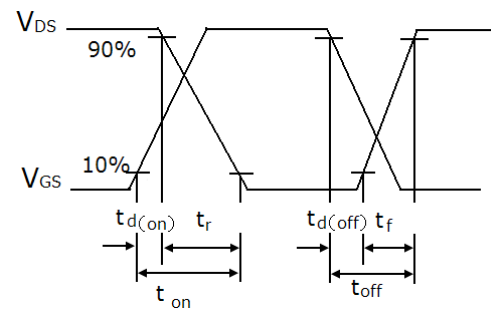
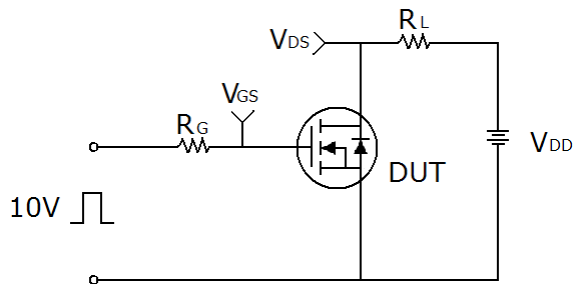


Test circuit

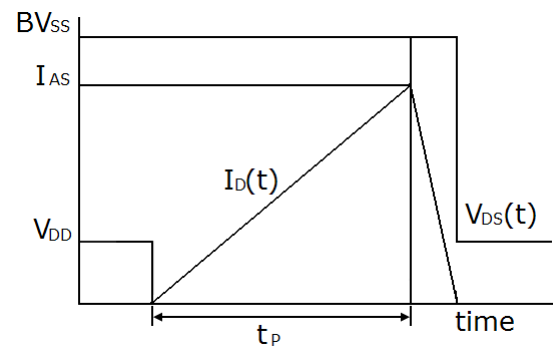
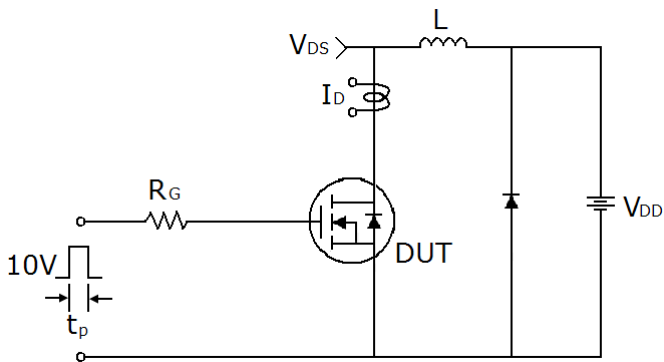
1) Gate charge test circuit & Waveform



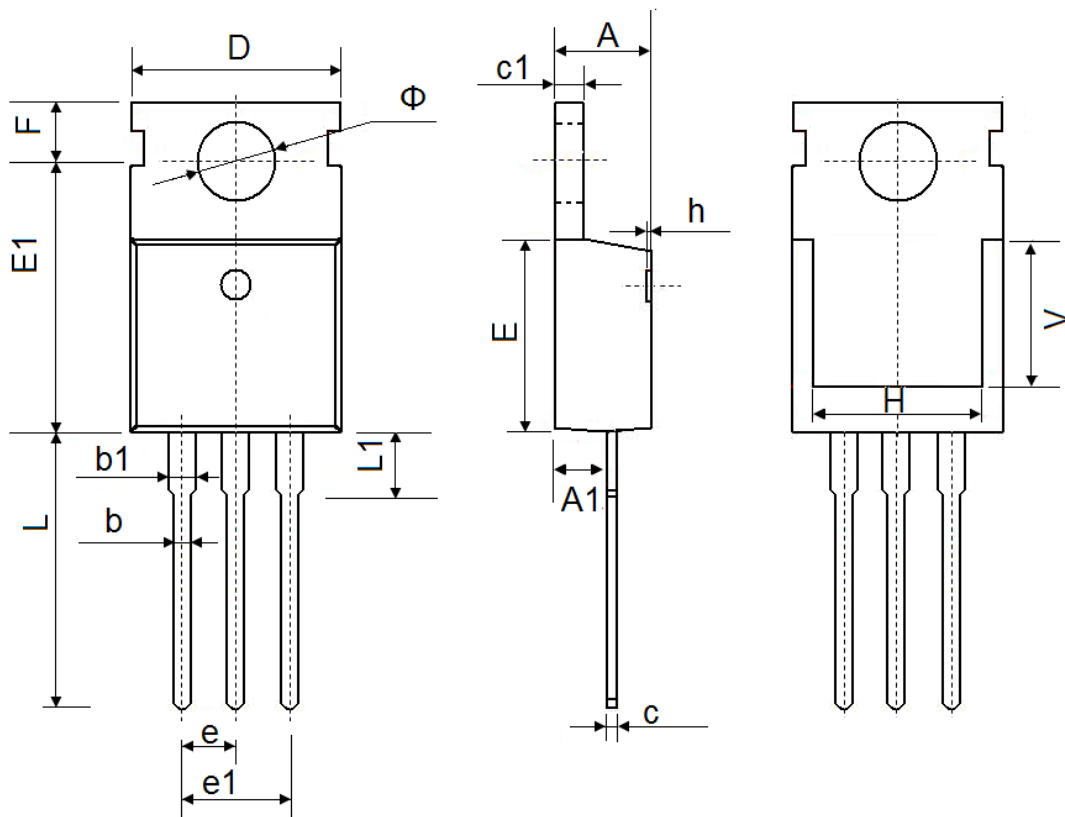
2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms

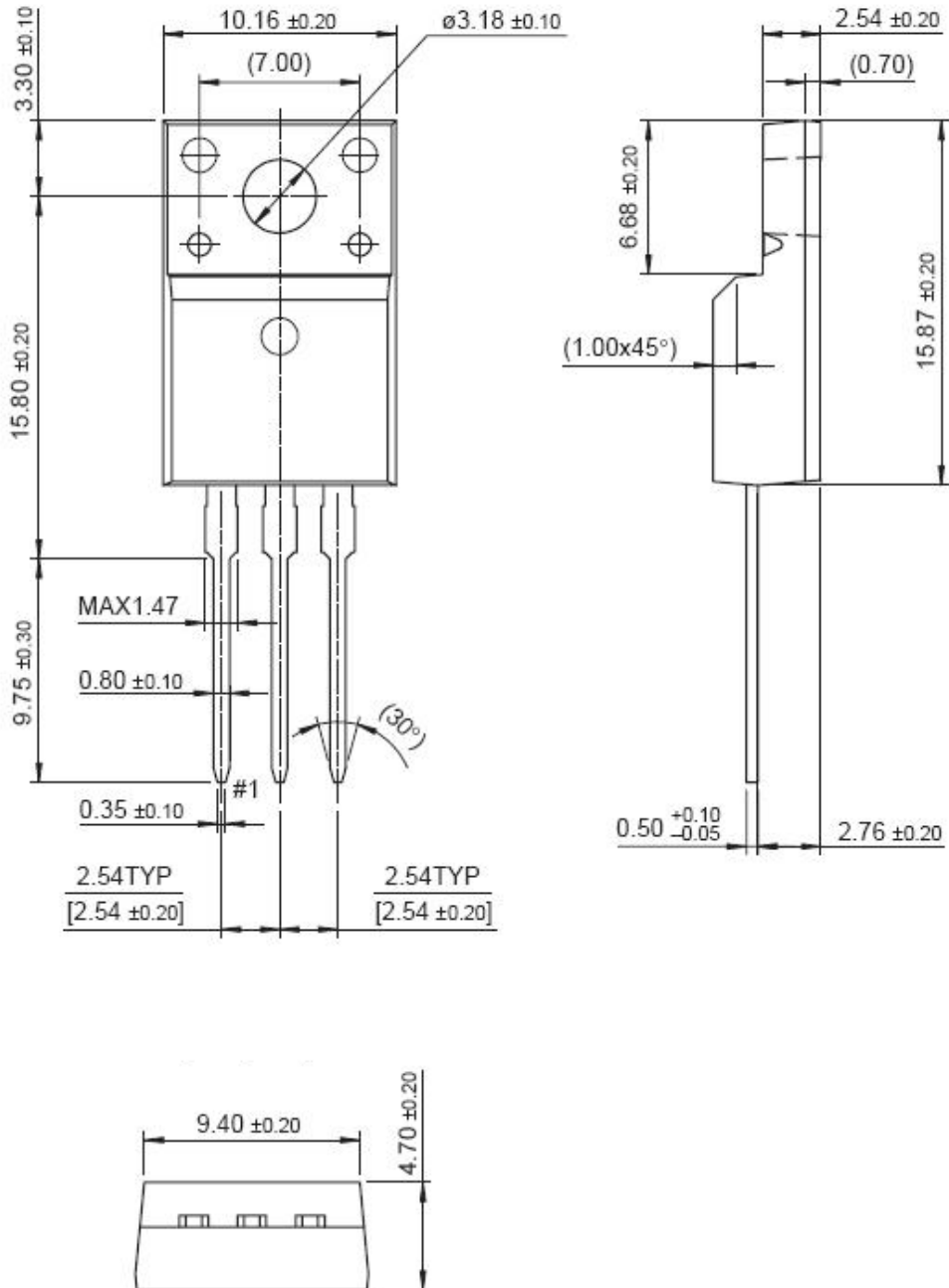


TO-220-3L-C Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150

TO-220F Package Information



Dimensions in Millimeters

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